

*East Search
in paper ad. 5*

L Number	Hits	Search Text	DB	Time stamp
-	23	("5795803" "6096611") ep-358246-\$.did. jp-03173172-\$.did. jp-05036917-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 14:45
-	26	"5384279" and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:20
-	0	substrate with most with conventionally with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:21
-	0	substrate with most with often with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:21
-	2204	substrate with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:21
-	13	substrate with most with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:23
-	2	substrate with commonly with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:24
-	14	substrate with usually with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:25
-	67	substrate with conductivity with p-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:27
-	4473	substrate with conductivity with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:27
-	14	substrate with conductivity with commonly with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:30
-	19	substrate with conductivity with advantages with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:31
-	35	substrate with conductivity with (generally usually conventionally) with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:48

-	0	substrate with p-type with conductivity with cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:48
-	0	substrate with p-type with conductivity and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:49
-	0	substrate with p-type with conductivity and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:49
-	1	substrate with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:50
-	0	substrate with p-type and twin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:50
-	1	substrate with p-type and well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:50
-	668	substrate with conductivity with cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:51
-	5524	substrate with conductivity and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:51
-	3726	substrate near3 conductivity and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:51
-	494	substrate near1 conductivity and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:52
-	6	(substrate near1 conductivity) with most and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 15:53
-	23	substrate with conductivity with commonly and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:03
-	4473	substrate with conductivity with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:03
-	0	substrate with conductivity with p-type with widely	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:05

-	1	substrate with conductivity with p-type with most adj commonly	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:06
-	154	substrate with conductivity with p-type with typically	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:07
-	0	substrate with conductivity with p-type with nost adj typically	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:07
-	0	substrate with conductivity with p-type with most adj typically	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:08
-	50	(substrate with conductivity with p-type with typically) and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:32
-	2	5401671.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:59
-	21704	semiconductor with substrate with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 16:59
-	0	semiconductor with substrate with most adj commonly with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:06
-	12	semiconductor with substrate with commonly with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:11
-	17	semiconductor with substrate with conventionally with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:12
-	96	semiconductor with substrate with typically with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:14
-	2	semiconductor with substrate with widely with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:13
-	0	semiconductor with substrate with generally with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:14
-	20	semiconductor with substrate with usually with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:19

-	0	semiconductor with substrate with most adj often with p-type and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:19
-	30	semiconductor with substrate with most adj widely adj used	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:29
-	317423	substrate.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:29
-	2560	substrate.ti. and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:30
-	502	(substrate.ti. and cmos) and substrate with p-type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:30
-	509	((substrate.ti. and cmos) and substrate with p-type) and (p-type).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:30
-	93	((substrate.ti. and cmos) and substrate with p-type) and (p-type).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:57
-	2	5061646.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 17:57
-	20	"5061646"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:00
-	9	"4266237"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:04
-	2999	(highly heavily) adj doped near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:07
-	786	(highly heavily) adj doped near2 substrate with epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:08
-	400	(highly heavily) adj doped adj substrate with epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:11
-	84323	(highly heavily) adj doped adj substrate with lighthly adj doped epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:10

-	0	(highly heavily) adj doped adj substrate with lighthly adj doped adj epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:10
-	0	(highly heavily) adj doped adj substrate with lighthly adj doped with epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:10
-	0	(highly heavily) adj doped adj substrate with lighthly adj doped with epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:11
-	0	(highly heavily) adj doped adj substrate with lighthly adj doped with epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:11
-	114	((highly heavily) adj doped adj substrate with epitaxial\$2) and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 18:12
-	0	2002us-0137349-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 11:07
-	0	2002us-0137349-.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 11:07
-	0	2002us-137349-.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 11:07
-	0	2002us-137349-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 11:08
-	7	(US-4435895-\$ or US-4590663-\$ or US-5899732-\$ or US-4947228-\$.did. or (US-20020137349-\$.did. or (EP-271749-\$ or EP-337550-\$.did.	USPAT; US-PGPUB; DERWENT	2002/10/01 11:12
-	2	6307247.pn.	USPAT; US-PGPUB; DERWENT	2002/10/01 11:12